

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1721

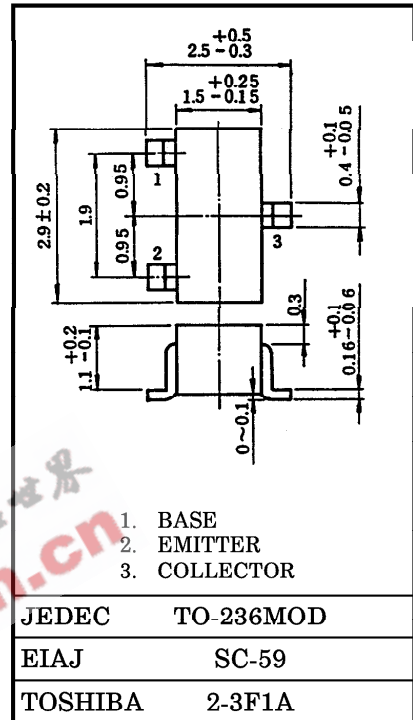
Unit in mm

HIGH VOLTAGE CONTROL APPLICATIONS.  
 PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS.  
 CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS.

- High Voltage :  $V_{CBO} = -300V$ ,  $V_{CEO} = -300V$
- Low Saturation Voltage :  $V_{CE(sat)} = -0.5V$  (Max.)
- Small Collector Output Capacitance :  $C_{ob} = 5.5pF$  (Typ.)
- Complementary to 2SC4497

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-300	V
Collector-Emitter Voltage	$V_{CEO}$	-300	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-100	mA
Base Current	$I_B$	-20	mA
Collector Power Dissipation	$P_C$	150	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



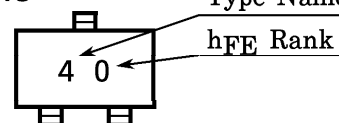
Weight : 0.012g

ELECTRICAL CHARACTERISTIC ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	$I_{CBO}$	$V_{CB} = -300V, I_E = 0$	—	—	-0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	$\mu A$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-300	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -10V, I_C = -20mA$	30	—	150	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$	—	—	-0.5	V
Base-Base Saturation Voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$	—	—	-1.2	V
Transition Frequency	$f_T$	$V_{CE} = -10V, I_C = -20mA$	50	55	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -20V, I_E = 0, f = 1MHz$	—	5.5	6.0	pF

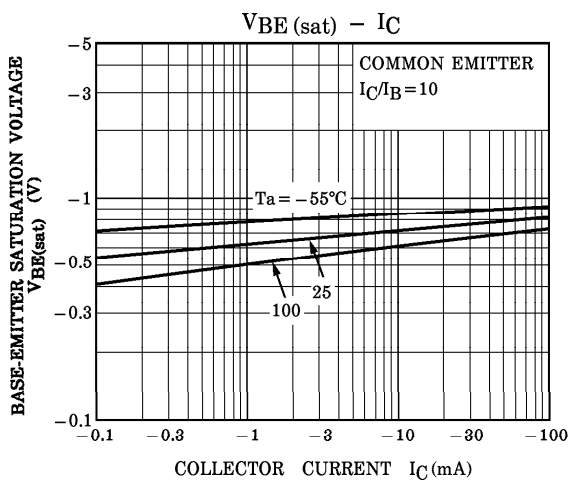
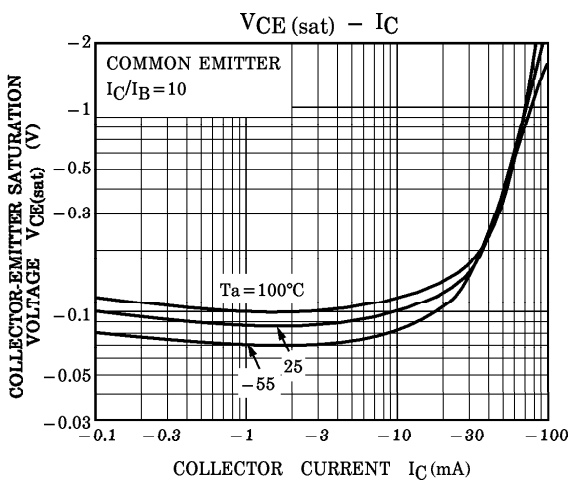
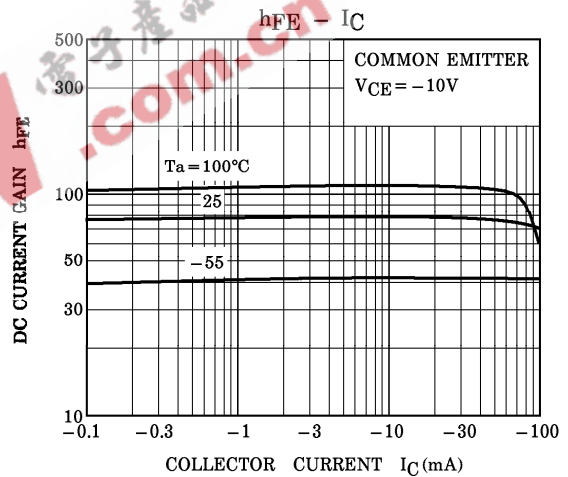
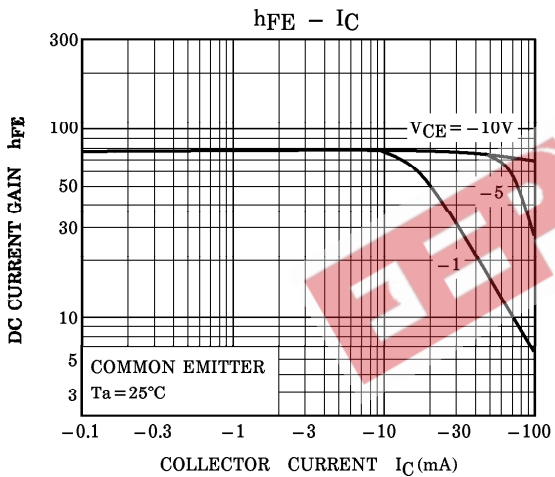
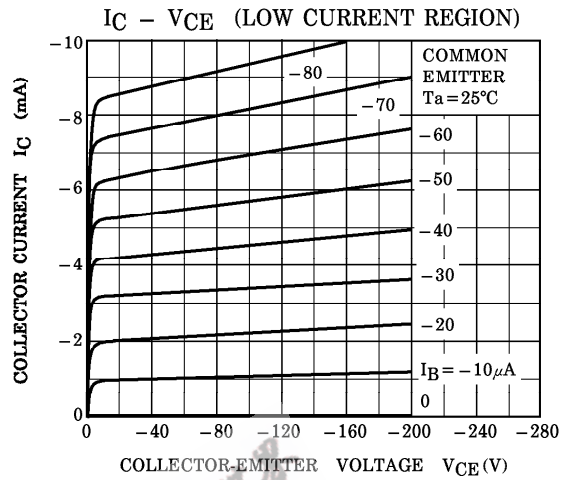
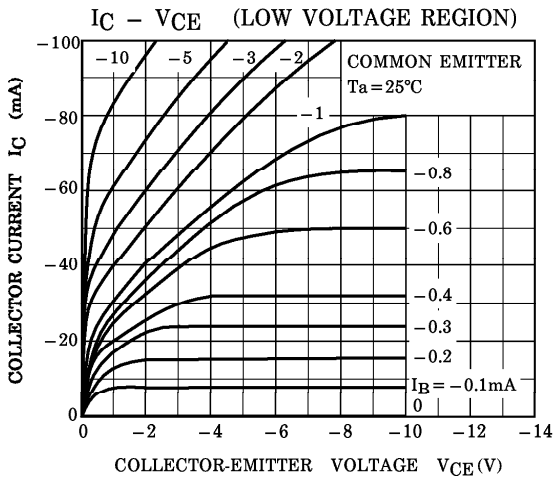
Note :  $h_{FE(1)}$  Classification R: 30~90 0: 50~150 MARKING

Type Name



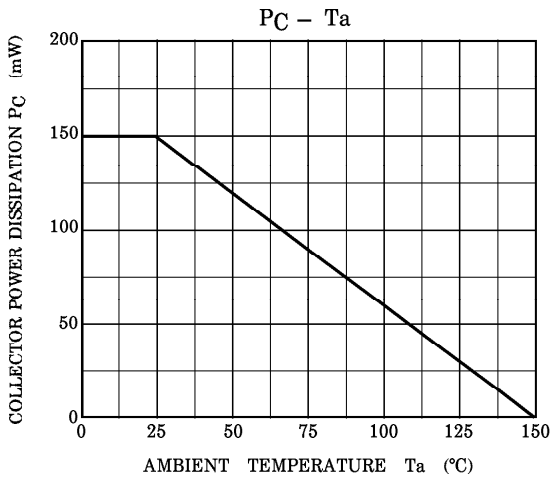
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